



10/06/2006

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Atty. Docket: SA'AR1
Amir SA'AR) Conf. No.: 9434
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 Filed: April 20, 2004) Washington, D.C.
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 U.S. Appln. No.: 10/554,113)
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 For: VOLTAGE TUNABLE INTEGRATED) October 6, 2006
 INFRARED IMAGER)

COMMUNICATION TO CORRECT BN/SB/08A/B

U.S. Patent and Trademark Office
Customer Service Window
Randolph Building, Mail Stop Amendment
401 Dulany Street
Alexandria, VA 22314

Sir:

The BN/SB/08A/B previously filed with an Information Disclosure Statement on August 21, 2006 had errors for references **AJ** and **AK**. Attached hereto is a clean copy of the BN/SB/08A/B identifying the accurate reference information for **AJ** and **AK**.

It is respectfully requested that the attached clean copy of BN/SB/08A/B replace the BN/SB/08A/B originally submitted with the Information Disclosure Statement filed on

August 21, 2006, and be entered into the file to correct the record.

Respectfully submitted,

BROWDY AND NEIMARK, P.L.L.C.
Attorneys for Applicant(s)

By



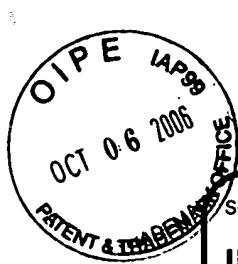
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Substitute for form 1449A/PTO

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(use as many sheets as necessary)

Sheet

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of

3

Complete if Known

Application Number 10/554,113

Filing Date April 20, 2004

First Named Inventor Amir SA'AR

Group Art Unit

Examiner Name

Attorney Docket Number SA'AR1

NON PATENT LITERATURE DOCUMENTS / OTHER INFORMATION

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T ²
	AJ	LUI, H et al., "Near and middle infrared dual band operation of InGaAs/InP quantum well infrared Photodetector"; Electronics Letters, Vol. 35, Issue 23, p.2055, 11 November 1999	
	AK	GUNAPALA, S.D. et al., "Lattice-matched InGaAsP/InP long-wavelength quantum well infrared photodetectors"; Appl. Phys. Lett, Vol. 60, No. 5, pp.636-638, 3 February 1992	
	AL	FORREST, S.R., "Performance of In _x Ga _{1-x} AsP _{1-y} Photodiodes with Dark Current Limited by Diffusion, Recombination, and Tunneling"; IEEE J. Quantum Electron, Vol. 17, No. 2, pp. 217-226, February 1981	
	AM	LEHENY, R.F. et al., "Characterization of In _{0.53} Ga _{0.47} As Photodiodes Exhibiting Low Dark Current and Low Junction Capacitance"; IEEE Journal of Quantum Electronics, Vol. 17, No. 2, pp. 227-231,February 1981	
	AN	LEE, T.P. et al., "InGaAs/InP p-i-n Photodiodes for Lightwave Communications at the 0.95-1.65 μm Wavelength"; IEEE Journal of Quantum Electronics, Vol. 17, No. 2, pp. 232-238, February 1981	
	AO	SUSA, N. et al., "Characteristics in InGaAs/InP Avalanche Photodiodes with Separated Absorption and Multiplication Regions"; IEEE Journal of Quantum Electronics, Vol. 17, No. 2, pp. 243-249, February 1981	
	AP	CAMPBELL, J.C. et al. "InP/InGaAs Heterojunction Phototransistors"; IEEE Journal of Quantum Electronics, Vol. 17, No. 2, pp264-269, February 1981	
	AQ	COHEN, N. et al; "A monolithic LWIR/NIR multispectral QWIP for night vision and see spot"; Infrared Physics and Technology; XP-002299329, Vol. 42, No. 3-5, pp.391-396, September 2001	
	AR	SCHNEIDER, H et al., "Voltage-tunable two-color detection by interband and intersubband transitions in a p-i-n-i-n structure"; Applied Physics Letters, Vol. 68, No. 13, pp.1832-1834, March 25, 1996	
	AS	RYZHII, V et al., "Device Model of Integrated QWIP-HBT-LED Pixel for Infrared Focal Plane Arrays"; Proceedings of the 32 nd European Solid-State Device Research Conference University; pp. 643-646, September 2002	
	AT	RYZHII, V et al., "Analysis of dual-band quantum well photodetectors"; Journal of Applied Physics; Vol. 91, No. 9, pp. 5887-5891, May 1, 2002	
	AU	LIU, H.C. et al., "GaAs/AlGaAs quantum-well photodetector for visible and middle infrared dual-band detection"; Applied Physics Letters; Vol. 77, No. 16, pp. 2437-2439, October 16, 2000	

Examiner Signature	Date Considered
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* EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Applicant's unique citation designation number (optional). ² Applicant is to place a check mark here if English language Translation is attached.